74LVC1G08

Single 2-input AND gate Rev. 07 — 17 July 2007

Product data sheet

General description 1.

The 74LVC1G08 provides one 2-input AND function.

Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in mixed 3.3 V and 5 V applications.

Schmitt trigger action at all inputs makes the circuit tolerant of slower input rise and fall time.

This device is fully specified for partial power-down applications using I_{OFF}.

The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. **Features**

- Wide supply voltage range from 1.65 V to 5.5 V
- High noise immunity
- Complies with JEDEC standard:
 - ◆ JESD8-7 (1.65 V to 1.95 V)
 - ◆ JESD8-5 (2.3 V to 2.7 V)
 - ◆ JESD8-B/JESD36 (2.7 V to 3.6 V)
- \pm 24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Latch-up performance ≤ 250 mA
- Direct interface with TTL levels
- Inputs accept voltages up to 5 V
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



3. Ordering information

Table 1. Ordering information

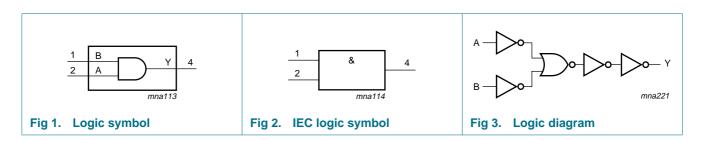
Type number	Package						
	Temperature range	Name	Description	Version			
74LVC1G08GW	–40 °C to +125 °C	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1			
74LVC1G08GV	–40 °C to +125 °C	SC-74A	plastic surface-mounted package; 5 leads	SOT753			
74LVC1G08GM	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body $1 \times 1.45 \times 0.5$ mm	SOT886			
74LVC1G08GF	–40 °C to +125 °C	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; body $1 \times 1 \times 0.5$ mm	SOT891			

4. Marking

Table 2. Marking

Type number	Marking code
74LVC1G08GW	VE
74LVC1G08GV	V08
74LVC1G08GM	VE
74LVC1G08GF	VE

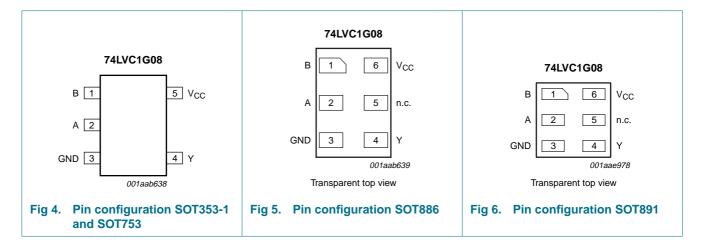
5. Functional diagram



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6. Pinning information

6.1 Pinning



6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description	
	SOT353-1/SOT753	SOT886/SOT891	
В	1	1	data input
A	2	2	data input
GND	3	3	ground (0 V)
Υ	4	4	data output
n.c.	-	5	not connected
V _{CC}	5	6	supply voltage

7. Functional description

Table 4. Function table[1]

Input		Output
A	В	Υ
L	L	L
L	Н	L
Н	L	L
Н	Н	Н

[1] H = HIGH voltage level; L = LOW voltage level

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+6.5	V
I_{IK}	input clamping current	V _I < 0 V	-50	-	mA
V_{I}	input voltage		<u>[1]</u> –0.5	+6.5	V
I _{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V	-	±50	mA
V_{O}	output voltage	Active mode	[<u>1][2]</u> –0.5	$V_{CC} + 0.5$	V
		Power-down mode	[<u>1][2]</u> –0.5	+6.5	V
Io	output current	$V_O = 0 V \text{ to } V_{CC}$	-	±50	mA
I _{CC}	quiescent supply current		-	100	mA
I_{GND}	ground current		-100	-	mA
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C} \text{ to } +125 ^{\circ}\text{C}$	<u>[3]</u> _	250	mW
T _{stg}	storage temperature		-65	+150	°C

^[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		1.65	-	5.5	V
VI	input voltage		0	-	5.5	V
Vo	output voltage	Active mode	0	-	V_{CC}	V
		V _{CC} = 0 V; Power-down mode	0	-	5.5	V
T _{amb}	ambient temperature		-40	-	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 1.65 \text{ V to } 2.7 \text{ V}$	-	-	20	ns/V
		V _{CC} = 2.7 V to 5.5 V	-	-	10	ns/V

^[2] When $V_{CC} = 0 \text{ V}$ (Power-down mode), the output voltage can be 5.5 V in normal operation.

^[3] For TSSOP5 and SC-74A packages: above 87.5 °C the value of P_{tot} derates linearly with 4.0 mW/K. For XSON6 packages: above 45 °C the value of P_{tot} derates linearly with 2.4 mW/K.

10. Static characteristics

Static characteristics Table 7.

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40	°C to +8	5 °C	–40 °C to	+125 °C	Unit
			Min	Typ[1]	Max	Min	Max	
V _{IH}	HIGH-level	V _{CC} = 1.65 V to 1.95 V	0.65V _{CC}	-	-	0.65V _{CC}	-	V
	input voltage	V _{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		V _{CC} = 2.7 V to 3.6 V	2.0	-	-	2.0	-	V
		V _{CC} = 4.5 V to 5.5 V	$0.7V_{CC}$	-	-	$0.7V_{CC}$	-	V
V _{IL}	LOW-level	V _{CC} = 1.65 V to 1.95 V	-	-	0.35V _{CC}	-	0.35V _{CC}	V
	input voltage	V _{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		V _{CC} = 2.7 V to 3.6 V	-	-	0.8	-	0.8	V
		V _{CC} = 4.5 V to 5.5 V	-	-	$0.3V_{CC}$	-	$0.3V_{CC}$	V
V _{OH}	HIGH-level	$V_I = V_{IH}$ or V_{IL}						
	output voltage	$I_O = -100 \mu A;$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	V _{CC} – 0.1	-	-	V _{CC} – 0.1	-	V
		$I_{O} = -4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	1.2	-	-	0.95	-	V
		$I_{O} = -8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	1.9	-	-	1.7	-	V
		$I_{O} = -12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.2	-	-	1.9	-	V
		$I_{O} = -24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.3	-	-	2.0	-	V
		$I_{O} = -32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	3.8	-	-	3.4	-	V
V _{OL} LOW-level		$V_I = V_{IH}$ or V_{IL}						
	output voltage	$I_O = 100 \mu A;$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	-	-	0.10	-	0.10	V
		$I_O = 4 \text{ mA}; V_{CC} = 1.65 \text{ V}$	-	-	0.45	-	0.70	V
		$I_O = 8 \text{ mA}; V_{CC} = 2.3 \text{ V}$	-	-	0.30	-	0.45	V
		$I_{O} = 12 \text{ mA}; V_{CC} = 2.7 \text{ V}$	-	-	0.40	-	0.60	V
		$I_O = 24 \text{ mA}; V_{CC} = 3.0 \text{ V}$	-	-	0.55	-	0.80	V
		$I_O = 32 \text{ mA}; V_{CC} = 4.5 \text{ V}$	-	-	0.55	-	0.80	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	±0.1	±5	-	±100	μΑ
l _{OFF}	power-off leakage current	$V_{CC} = 0 \text{ V}; V_{I} \text{ or } V_{O} = 5.5 \text{ V}$	-	±0.1	±10	-	±200	μΑ
I _{CC}	supply current	$V_I = 5.5 \text{ V or GND; } I_O = 0 \text{ A;}$ $V_{CC} = 1.65 \text{ V to } 5.5 \text{ V}$	-	0.1	10	-	200	μΑ
Δl _{CC}	additional supply current	per pin; $V_{CC} = 2.3 \text{ V to } 5.5 \text{ V};$ $V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0 \text{ A}$	-	5	500	-	5000	μΑ
Cı	input capacitance	V_{CC} = 3.3 V; V_I = GND to V_{CC}	-	5	-	-	-	pF

^[1] All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for load circuit see Figure 8.

Symbol	Parameter	Conditions		–40 °C to +85 °C			–40 °C to +125 °C		Unit
			M	lin	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	A, B to Y; see Figure 7	2]						
		$V_{CC} = 1.65 \text{ V to } 1.95 \text{ V}$	1	.0	3.4	8.0	1.0	10.5	ns
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	0).5	2.2	5.5	0.5	7.0	ns
		$V_{CC} = 2.7 \text{ V}$	0).5	2.5	5.5	0.5	7.0	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	0).5	2.1	4.5	0.5	6.0	ns
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0).5	1.7	4.0	0.5	5.5	ns
C_{PD}	power dissipation capacitance	$V_I = GND \text{ to } V_{CC}; V_{CC} = 3.3 \text{ V}$	3]	-	16	-	-	-	pF

- [1] Typical values are measured at $T_{amb} = 25$ °C and $V_{CC} = 1.8$ V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.
- [2] t_{pd} is the same as t_{PLZ} and t_{PZL} .
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \sum (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

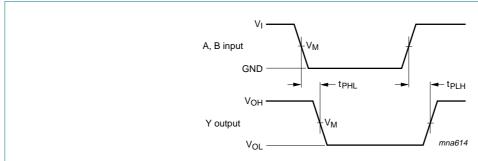
C_L = output load capacitance in pF;

 V_{CC} = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}^2 \times f_0)$ = sum of outputs.

12. AC waveforms



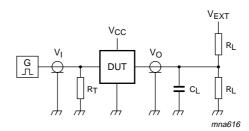
Measurement points are given in Table 9.

 V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 7. The input A, B to output Y propagation delays

Table 9. Measurement points

Supply voltage	Input	Output
V _{CC}	V _M	V _M
1.65 V to 1.95 V	0.5V _{CC}	0.5V _{CC}
2.3 V to 2.7 V	0.5V _{CC}	0.5V _{CC}
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	0.5V _{CC}	0.5V _{CC}



Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 8. Load circuitry for switching times

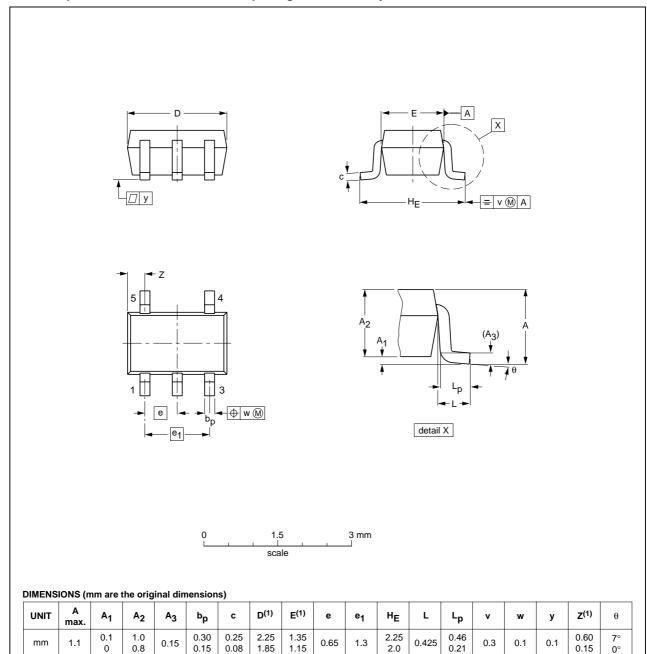
Table 10. Test data

Supply voltage	Input		Load		V _{EXT}
V _{CC}	Vı	$t_r = t_f$	CL	R_L	t _{PLH} , t _{PHL}
1.65 V to 1.95 V	V _{CC}	≤ 2.0 ns	30 pF	1 kΩ	open
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	$500~\Omega$	open
2.7 V	2.7 V	≤ 2.5 ns	50 pF	$500~\Omega$	open
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	$500~\Omega$	open
4.5 V to 5.5 V	V _{CC}	≤ 2.5 ns	50 pF	$500~\Omega$	open

13. Package outline

TSSOP5: plastic thin shrink small outline package; 5 leads; body width 1.25 mm

SOT353-1



1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE	OUTLINE REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT353-1		MO-203	SC-88A			-00-09-01 03-02-19

Fig 9. Package outline SOT353-1 (TSSOP5)

Plastic surface-mounted package; 5 leads

SOT753

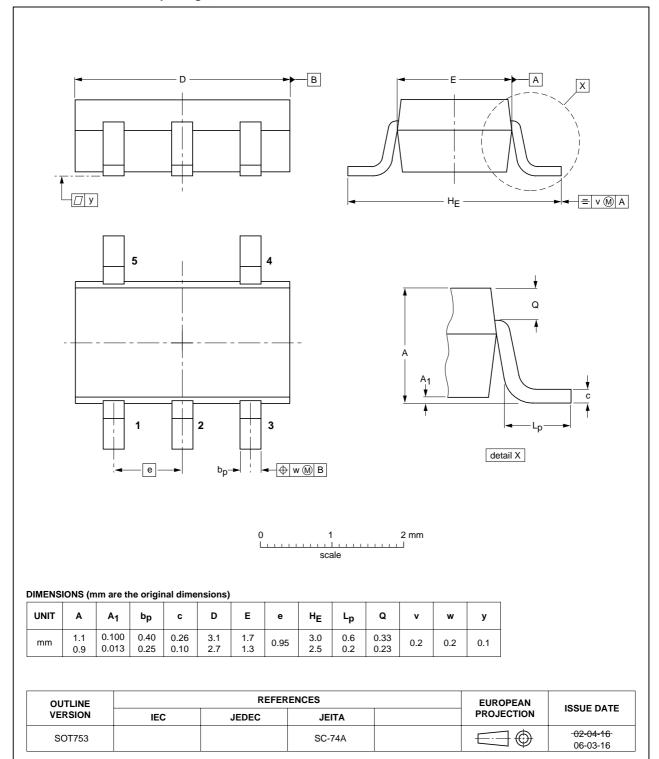


Fig 10. Package outline SOT753 (SC-74A)

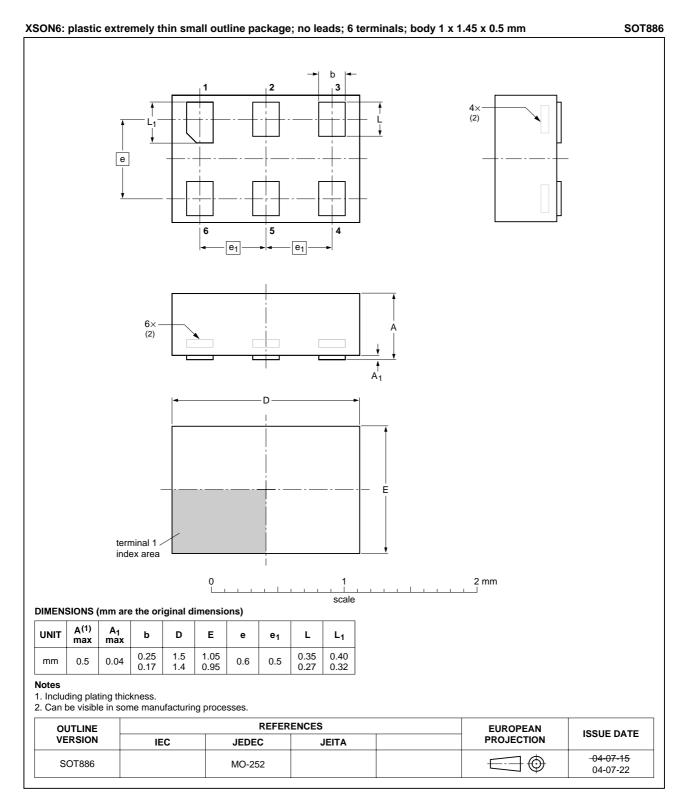


Fig 11. Package outline SOT886 (XSON6)

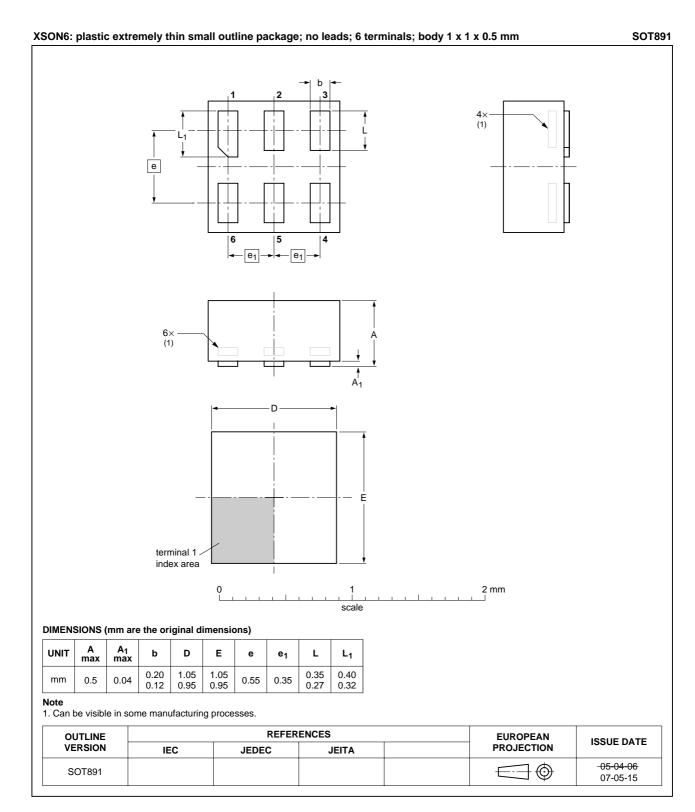


Fig 12. Package outline SOT891 (XSON6)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
74LVC1G08_7	20070717	Product data sheet	-	74LVC1G08_6	
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 				
	 Legal texts have been adapted to the new company name where appropriate. 				
	• Section 10 "Static characteristics":				
	Changed: Co	onditions for input leakage cu	irrent and supply curre	ent.	
	 New packag 	e outline drawing for XSON6	/SOT891.		
74LVC1G08_6	20060619	Product data sheet	-	74LVC1G08_5	
74LVC1G08_5	20040915	Product specification	-	74LVC1G08_4	
74LVC1G08_4	20021002	Product specification	-	74LVC1G08_3	
74LVC1G08_3	20020517	Product specification	-	74LVC1G08_2	
74LVC1G08_2	20010406	Product specification	-	74LVC1G08_1	
74LVC1G08_1	20001121	Product specification	-	-	

16. Legal information

16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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NXP Semiconductors

74LVC1G08

Single 2-input AND gate

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